

Form PTO-1449	ATTORNEY DOCKET NO. 10021234-1	SERIAL NO. TBA
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	APPLICANT Leary <i>et al.</i>	
	FILING DATE October 17, 2003	GROUP TBA

(Use several sheets if necessary)

REFERENCE DESIGNATION		U.S. PATENT DOCUMENTS		
EXAMINER INITIAL	*	DOCUMENT NUMBER	DATE	NAME

FOREIGN PATENT DOCUMENTS					
		DOCUMENT NUMBER	DATE	NAME	TRANSLATION YES NO

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, etc.)		
PN	AA	R. Shau <i>et al.</i> , Vertical-cavity Surface-emitting Laser Diodes at 1.55- $\mu$ m With Large Output Power and High Operation Temperature, <i>Electronics Letters</i> , October 11, 2001, Vol. 37 No. 21 (1295)
	BB	S. Nakagawa <i>et al.</i> , 1.55- $\mu$ m InP-Lattice-Matched VCSELs With AlGaAsSb-AlAsSb DBRs, <i>IEEE Journal on Selected Topics in Quantum Electronics</i> , Vol. 7, No. 2, March/April 2001, 224-230
	CC	Chao-Kun Lin <i>et al.</i> High Temperature Continuous-Wave Operation of 1.3-1.55- $\mu$ m VCSELs With InP/Air-Gap DBRs
	DD	J. J. Wierer, <i>et al.</i> , Lateral Electron Current Operation of Vertical Cavity Surface Emitting Lasers With Buried Tunnel Contact Hole Sources, <i>Appl. Phys. Lett.</i> , Vol. 71, No. 24, December 15, 1997, 3468-3470
	EE	K. D. Choquette, <i>et al.</i> , Room Temperature Continuous Wave InGaAsN Quantum Well Vertical-Cavity Lasers Emitting at 1.3 $\mu$ m, <i>Electronics Letters</i> , August 3, 2000, Vol. 36, No. 16, 1388-1390
	FF	K. M. Yu, <i>et al.</i> , Nitrogen-Induced Increase of the Maximum Electron Concentration in Group III-N-V Alloys, <i>The American Physical Society</i> , Physical Review B, Vol. 61, Number 20, May 15, 2000, 337-340
	GG	K. M. Yu, <i>et al.</i> , Mutual Passivation of Electrically Active and Isovalent Impurities, <i>Nature Publishing Group</i> , Advance Online Publication, 1-5
	HH	W. Shan, <i>et al.</i> , Effect of Nitrogen on the Electronic Band Structure of Group III-N-V Alloys, <i>The American Physical Society</i> , Physical Review B, Vol. 62, Number 7, August 15, 2000.
	II	K. M. Yu, <i>et al.</i> , Mutual Passivation of Group IV Donors and Nitrogen in Diluted GaN <sub>1-x</sub> As <sub>1-x</sub> Alloys
EXAMINER	DATE CONSIDERED 1/17/06	

\* Copies of these references are not included Pursuant to 37 CFR 1.98(d). (See accompanying IDS)